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(71) Applicant: **HITACHI LTD**

(72) Inventor: **KOBAYASHI TAKASHI**

**IJIMA SHINPEI**

**HIRAIWA ATSUSHI**

**KOBAYASHI NOBUYOSHI**

**NANBA MITSUO**

**HASHIMOTO KOJI**

(74) Representative:

## (54) MANUFACTURE OF SEMICONDUCTOR DEVICE

(57) Abstract:

PURPOSE: To provide a method of manufacturing a silicon film including boron which ensures excellent step-portion covering characteristic and is just suitable for

manufacturing process under a low temperature condition.

**CONSTITUTION:** An amorphous Si film is deposited by the pressure-reduced CVD method under a low temperature of 200 or higher and 400°C or lower using any one of disilane ( $\text{Si}_2\text{H}_6$ ) or trisilane ( $\text{Si}_3\text{H}_8$ ) and dibolane ( $\text{B}_2\text{H}_6$ ). Thereby, a Si film including boron which ensures excellent step-portion covering characteristic can be formed. Using the obtained Si film as a diffusion source, extremely shallow junction may be formed.

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